

IN THE SPECIFICATION:

Please amend paragraph [0038] on page 11 of the specification as follows:

[0038] The line level dielectric and via level dielectric are dielectric materials having low dielectric constants ($k < 3$) and are thermally stable to temperatures greater than about 300°C. The preferred materials for the line level dielectric ~~32~~ 31 and via level dielectric ~~31~~ 32 are: polysiloxanes, polysilsesquioxanes, polyarylenes, poly(arylene ethers) and dielectrics that are generated by chemical vapor deposition approaches having the composition $\text{Si}_v\text{N}_w\text{C}_x\text{O}_y\text{H}_z$, where $0.05 \leq v \leq 0.8$, $0 \leq w \leq 0.9$, $0.05 \leq x \leq 0.8$, $0 \leq y \leq 0.8$, $0.05 \leq z \leq 0.8$ for $v+w+x+y+z=1$. The dielectric composition may also be $\text{Si}_v\text{N}_w\text{C}_x\text{O}_y\text{H}_z$, where $0.05 < v < 0.8$, $0 < w < 0.9$, $0.05 < x < 0.8$, $0 < y < 0.8$, $0.05 < z < 0.8$ for $v+w+x+y+z=1$. Optionally, the dielectric may be air or an inert gas. The low dielectric constant material may also be porous. In one embodiment the line level dielectric layer has a first composition and the via level dielectric has a second composition, where the first composition is different from the second composition.

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